

EM-NANO 2025 Timetable

Time	June 11, Wednesday	June 12, Thursday	June 13, Friday	June 14, Saturday	Time
9			9:00-9:30 (30 mins) on Nitride and Oxide based Wide bandgap Semiconductor Devices, Invited Lecture 1 To be announced	Plenary Lecture 3 "Novel approaches for responsible electronics" Prof. Karl Lao Technische Universität Dresden	9
10		Opening Remarks	9:30-10:00 (30 mins) Nitride and Oxide based Wide bandgap Semiconductor Devices, Invited Lecture 2 "High-Frequency Performance of AlGaN/GaN HEMTs with High Al Content: A Theoretical Study" Prof. Masaaki Kuzuhara, Kwansai Gakuin University		10
11		Plenary Lecture 1 "A New Era of SiC Power Devices and their Impacts on Carbon Neutrality" Prof. Tsunenobu Kimoto JSAP President, Kyoto University	10:00-10:30 (30 mins) Nitride and Oxide based Wide bandgap Semiconductor Devices, Invited Lecture 3 "Heteroepitaxy of Ga ₂ O ₃ films using liquid-injection MOCVD: Impact of Hydrogen annealing on transport properties of MOSFETs" Prof. Milan Tapajna, Slovak Academy of Science		11
12		10:45-11:00 (15 mins) Break	10:30-10:45 (15 mins) Break		12
13		Plenary Lecture 2 "A Renewed Challenge at Leading-Edge Semiconductors" Chairman Tetsuro Higashi Chairman of the Board of Directors at Rapidus Corporation	10:45-12:30 (105 mins) Session 5 (D8. Silicon LSI Emerging Tech)	10:15-12:00 (105 mins) Session 11 (D7. Spintronics)	13
14		Lunch	Lunch	Lunch	14
15		12:00-14:00 (2 hrs) Poster Session 1	12:30-14:30 (2 hrs) Poster Session 2	12:00-14:00 (2 hrs) Poster Session 3	15
16		14:00-15:45 (105 mins) Session 1 (A. Organic Materials and Devices for Electronic)	14:30-16:15 (105 mins) Session 7 (D1. Photovoltaics)	14:00-14:30 (30 mins) Session 13 (C. Nanotechnologies for Electronics)	16
17		16:00-18:00 (120 mins) Session 3 (D1. Photovoltaics)	16:15-16:40 (25 mins) Break	14:30-15:30 (60 mins) Session 14 (B. Inorganic Materials and Devices for Electronics)	17
18		18:00 ~ Welcome Reception	18:40-19:00 (20 mins) Break	18:00-19:00 (50 mins) Break	18
			19:00 ~ Banquet		